

JUL 15 2005

JUL-15-2005 15:41

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P. 06/35

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Jack O. CHU, et al. Examiner: Johannes P. MONDT

Serial No: 10/775,514 Art Unit: 2826

Filed: February 10, 2004 Docket: YOR920010308US3 (16315B)

For: EPITAXIAL AND POLYCRYSTALLINE Dated: July 15, 2005

GROWTH OF Si<sub>1-x</sub>Ge<sub>x</sub>C<sub>y</sub> AND Si<sub>1-x</sub>C<sub>y</sub>  
ALLOY LAYERS ON Si BY UHV-CVD

Confirmation Number: 10338

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

RESPONSE UNDER 37 C.F.R. § 1.111

Sir:

In response to the Office Action dated May 5, 2005, Applicants hereby submit the following amendments and remarks for entry of record in the above-identified patent application.

CERTIFICATION OF FACSIMILE TRANSMISSION

I hereby certify that this document is being filed in the United States Patent and Trademark Office on the date shown below via facsimile transmission to Mail Stop Amendment, Commissioner for Patents, PO Box 1450, Alexandria, VA 22313-1450 at United States Patent and Trademark Office facsimile transmission number (703) 872-9306.

Dated: July 15, 2005

Leslie S. Saivus, Ph.D.